N-Channel 250 V (D-S) MOSFET

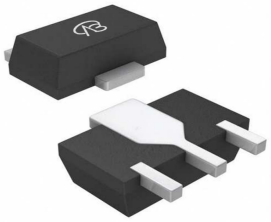
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
250	1.5 at V_{GS} = 10 V	0.3

FEATURES

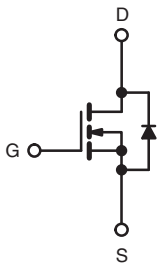
- **Halogen-free According to IEC 61249-2-21 Definition**
- 100 % R_g and UIS Tested
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

SOT89



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)					
Parameter		**Symbol**	**5 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	250		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	0.2	0.3	A
	T_A = 70 °C		0.15	0.2	
Pulsed Drain Current[b]		I_{DM}	0.5		
Avalanche Current[b]	L = 0.1 mH	I_{AS}	0.2		
Single Avalanche Energy		E_{AS}	0.1		mJ
Continuous Source Current (Diode Conduction)[a]		I_S	0.2		A
Power Dissipation[a]	T_A = 25 °C	P_D	1.55	1.03	W
	T_A = 70 °C		1.20	0.87	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 5 s	R_{thJA}	80	100	°C/W
	Steady State		130	170	
Maximum Junction-to-Foot	Steady State	R_{thJF}	45	55	

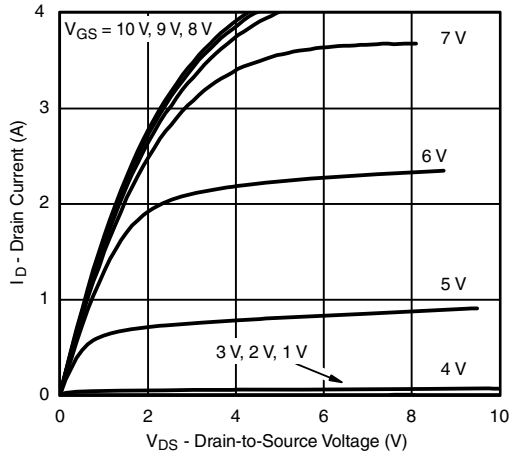
Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS (T_A = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 1 mA	250			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		3.0		
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 200 V, V_{GS} = 0 V			1	µA
		V_{DS} = 200 V, V_{GS} = 0 V, T_J = 70 °C			75	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 15 V, V_{GS} = 10 V	0.5			A
Drain-Source On-Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.1 A		1.5		Ω
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 0.1 A		4		S
Diode Forward Voltage	V_{SD}	I_S = 1 A, V_{GS} = 0 V		0.8	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 100 V, V_{GS} = 10 V, I_D = 0.2 A		3	5	nC
Gate-Source Charge	Q_{gs}			0.37		
Gate-Drain Charge	Q_{gd}			1.45		
Gate Resistance	R_g		0.5	1.3	2.4	Ω
Switching						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 100 V, R_L = 33 Ω $I_D \cong$ 0.2 A, V_{GEN} = 10 V, R_g = 6 Ω		7	11	ns
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			9	15	
Fall Time	t_f			11	15	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 0.2 A, dI/dt = 100 A/µs50100				

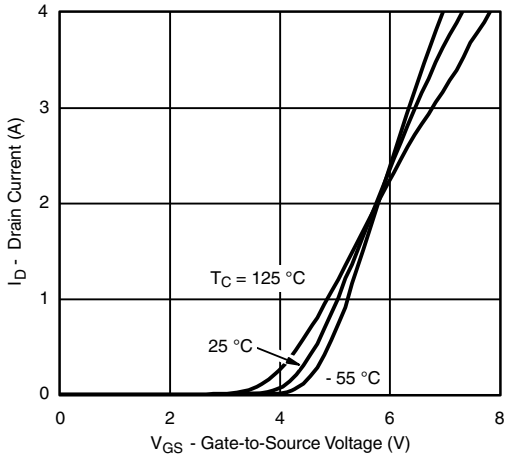
Notes:
a. Pulse test: PW ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

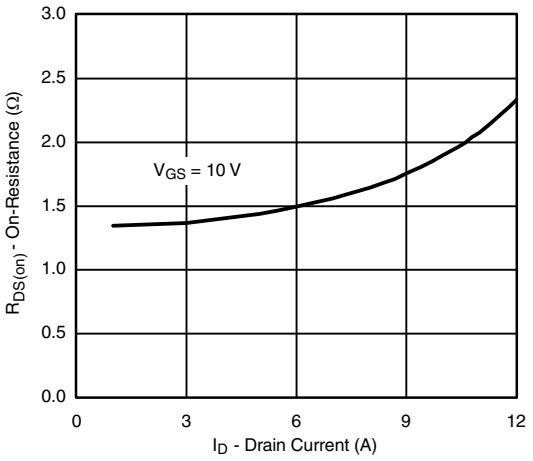


Output Characteristics

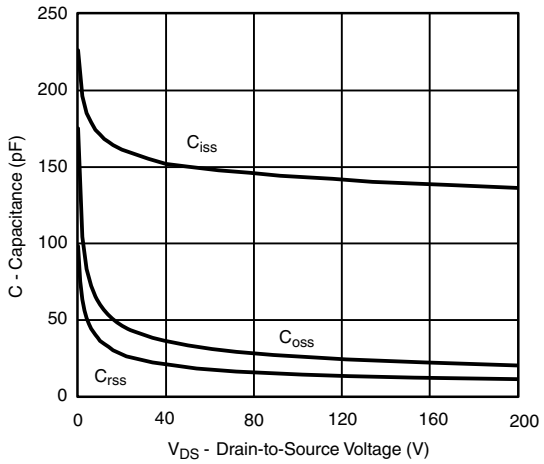


Transfer Characteristics

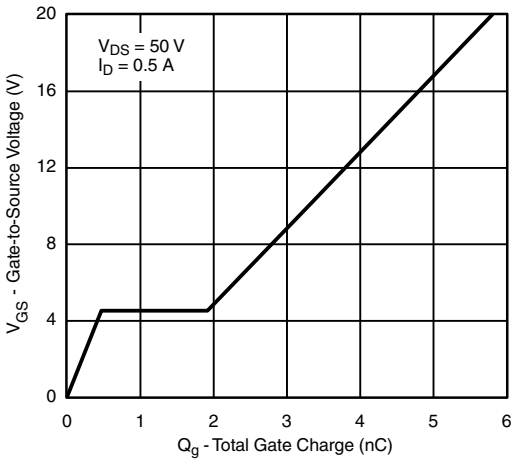
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



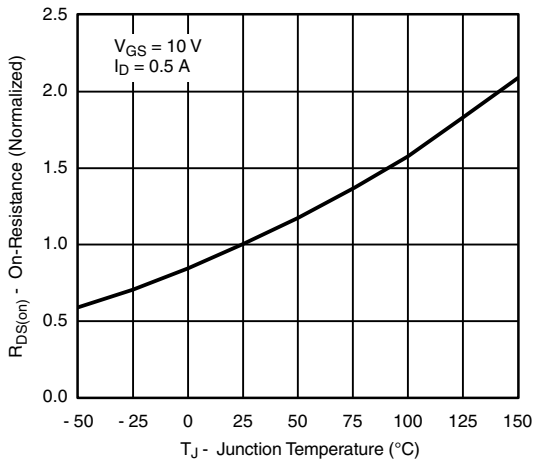
On-Resistance vs. Drain Current



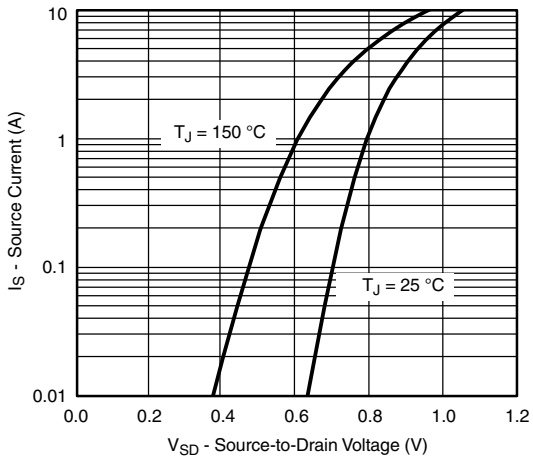
Capacitance



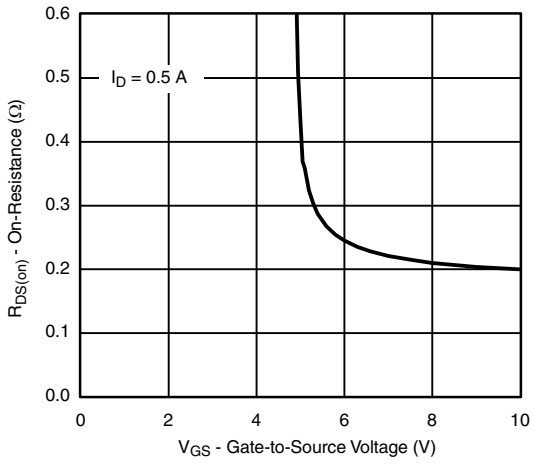
Gate Charge



On-Resistance vs. Junction Temperature

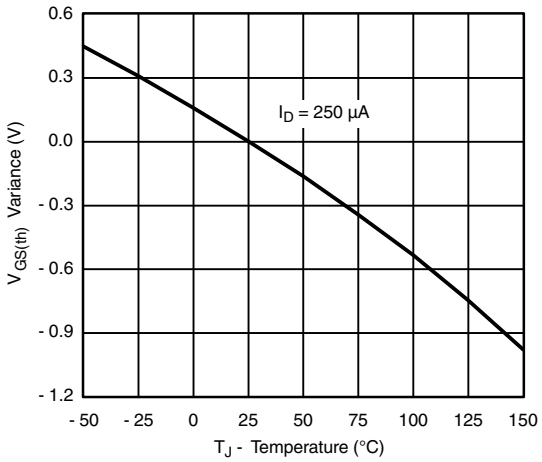


Source-Drain Diode Forward Voltage

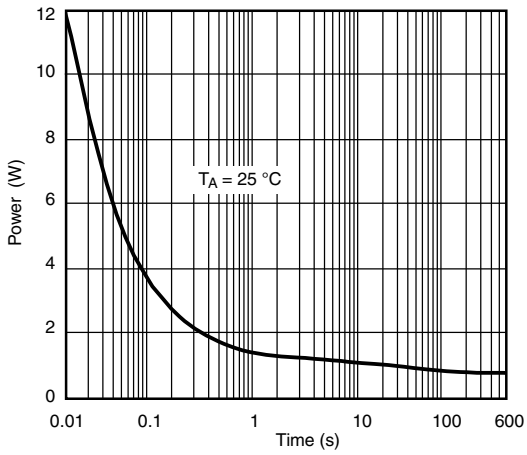


On-Resistance vs. Gate-to-Source Voltage

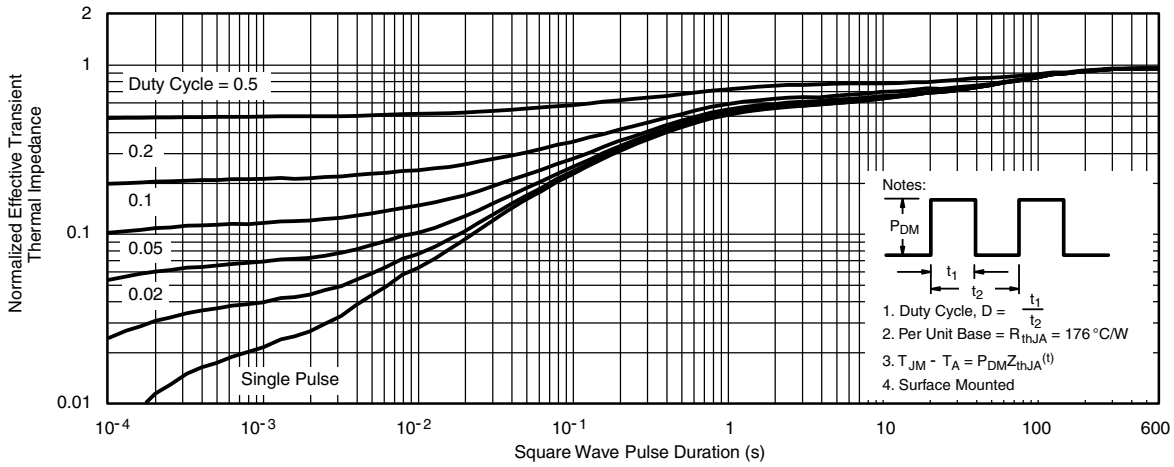
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Threshold Voltage

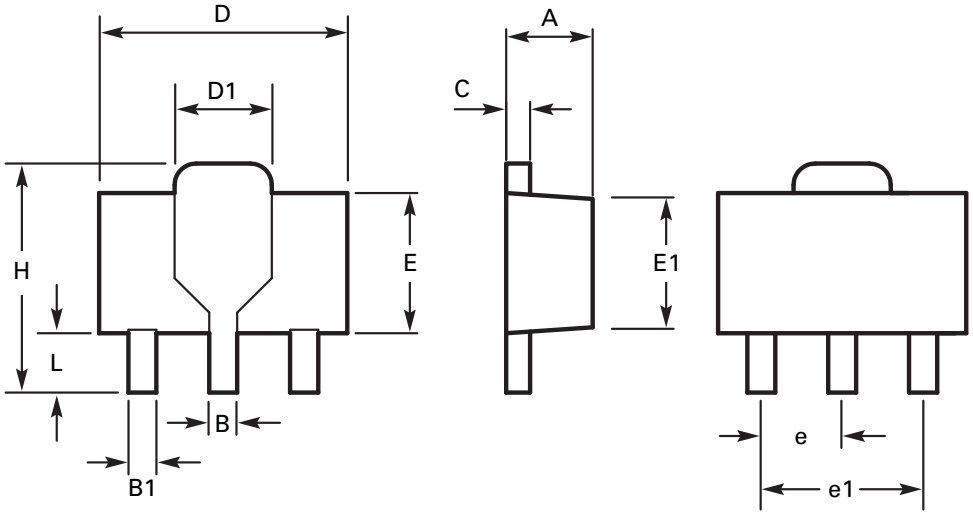


Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.62	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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